JS45B1GD20-2

1-Line Bi-directional TVS Diode

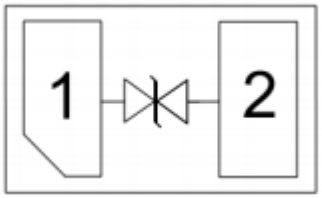
Description

The JS45B1GD20-2 is a Bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The JS45B1GD20-2 complies with the IEC 61000-4-2 (ESD) standard with ±30kV air and ±30kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm DFN package. The small size and high ESD surge protection make JS45B1GD20-2 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

* 400W peak pulse power (8/20μs)
* Low leakage：nA level
* Low operating voltage: 4.5V
* Ultra low clamping voltage
* One power line protects
* Complies with following standards:
  – IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±30kV
    Contact discharge: ±30kV
  – IEC61000-4-5 (Lightning) 40A (8/20μs)
* Package: DFN1006-2

Circuit Diagram



Circuit and Pin Schematic

Applications

* Cellular Handsets and Accessories
* Personal Digital Assistants
* Notebooks and Handhelds
* Portable Instrumentation
* Digital Cameras
* Peripherals
* Keypads, Side Keys, LCD Displays

Marking Diagram



Transparent top view

45:Device Marking Code

Ordering Information

Part Number	Packaging	Reel Size
JS45B1GD20-2	10000/Tape & Reel	7 inch

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

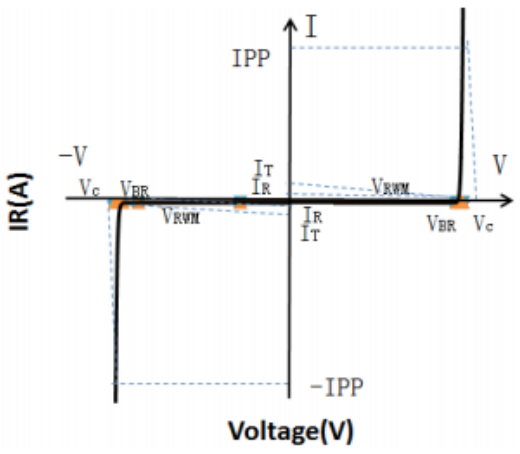
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	400	W
Peak Pulse Current (8/20μs)	IPP	40	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	VESD	±30 ±30	kV
Operating Temperature Range	TJ	−55to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

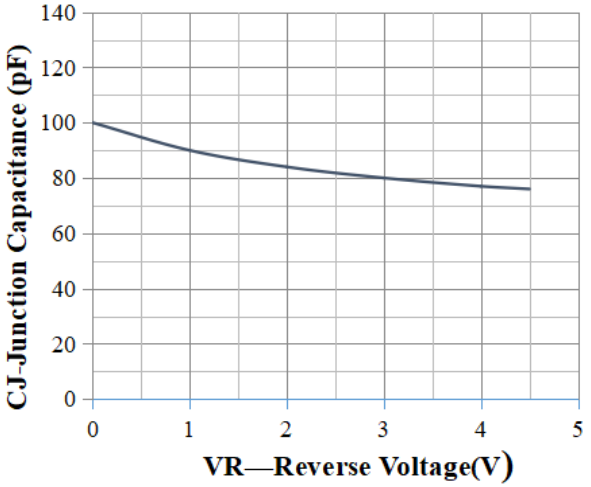
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				4.5	V
Breakdown Voltage	V_{BR}	I_T = 1mA	4.8			V
Reverse Leakage Current	I_R	V_{RWM} = 4.5V			0.2	μA
Clamping Voltage	V_C	I_{PP} = 1A (8 x 20μs pulse)			6.5	V
Clamping Voltage	V_C	I_{PP} = 40A (8 x 20μs pulse)			10	V
Junction Capacitance	C_J	VR = 0V, f = 1MHz		100		pF

Portion Electronics Parameter

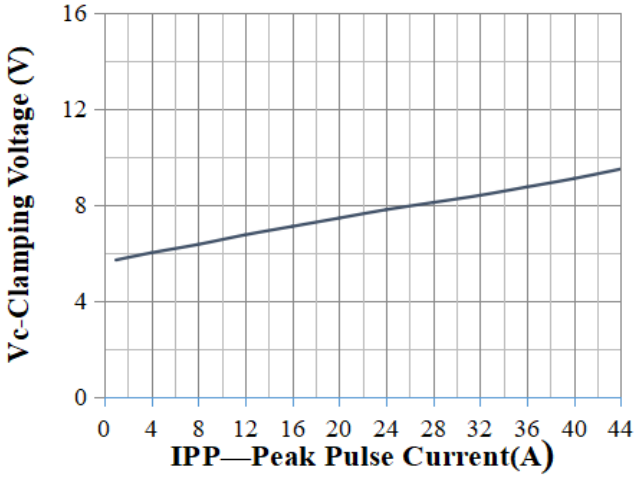
Symbol	Parameter
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @Ic



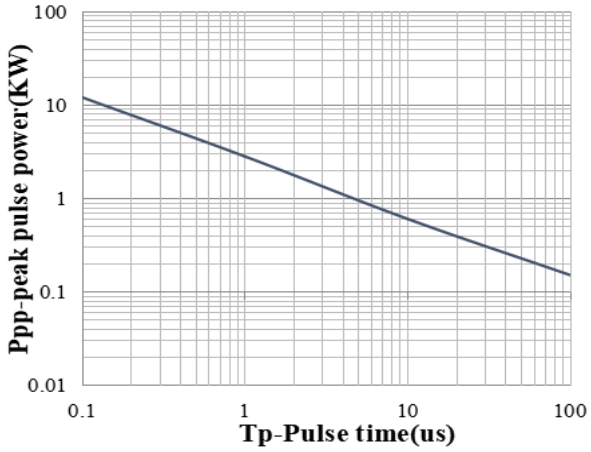
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



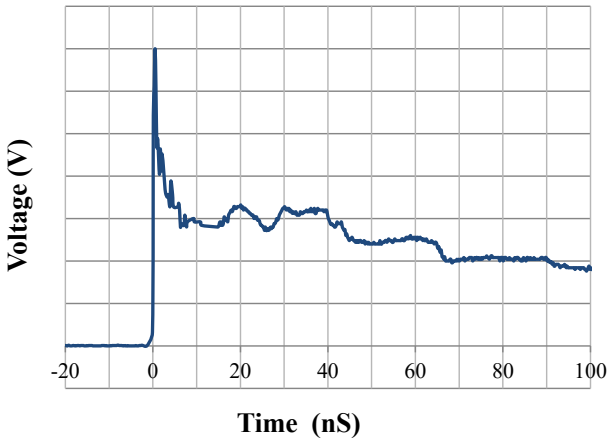
Junction Capacitance vs. Reverse Voltage



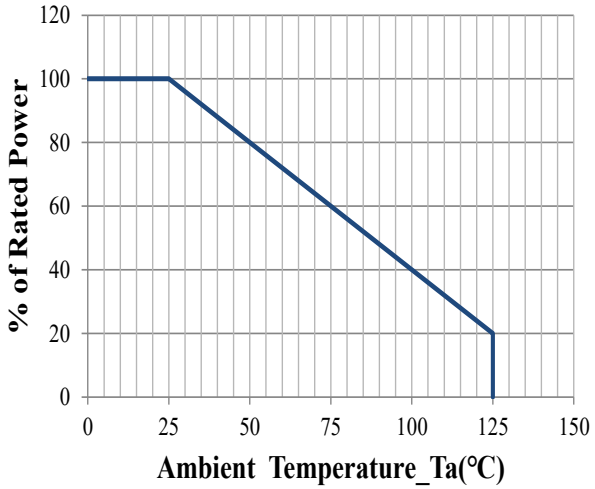
Clamping Voltage vs. Peak Pulse Current



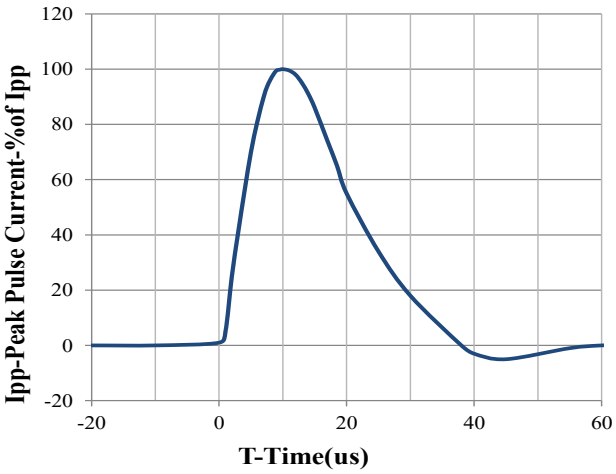
Peak Pulse Power vs. Pulse Time



IEC61000−4−2 Pulse Waveform

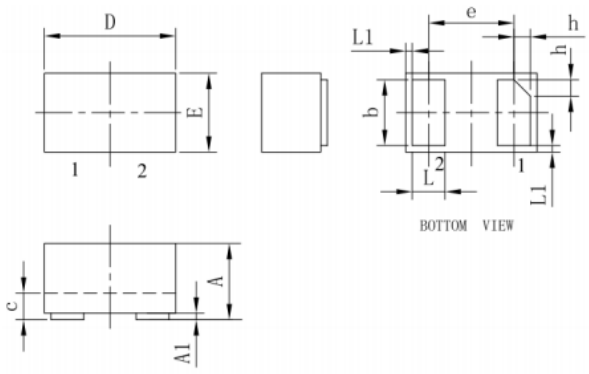


Power Derating Curve



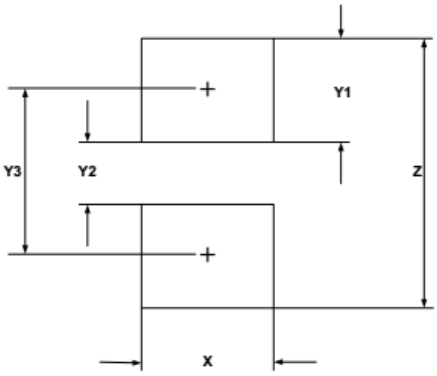
8 X 20us Pulse Waveform

DFN1006-2 Package Outline Drawing (Dimensions in millimeters)



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05REF			0.002REF		
h	0.07	0.12	0.17	0.003	0.005	0.007

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052

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